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Alek C. Chen
Burn Lin
Anthony Yen
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Contents

xv *Conference Committee*

EUVL TECHNOLOGY

- 7140 06 **EUVL contamination control studies for high-volume manufacturing (Invited Paper)** [7140-05]
D. N. Ruzic, R. Raju, J. Sporre, H. Shin, W. M. Lytle, M. J. Neumann, Univ. of Illinois at Urbana-Champaign (United States)
- 7140 07 **Full field EUV lithography: lessons learned on EUV ADT imaging, EUV resist, and EUV reticles** [7140-06]
E. Hendrickx, A. M. Goethals, IMEC (Belgium); A. Niroomand, IMEC (Belgium) and Micron Technology, Inc. (Belgium); R. Jonckheere, F. Van Roey, G. F. Lorusso, J. Hermans, B. Baudemprez, K. Ronse, IMEC (Belgium)
- 7140 08 **Current benchmarking results of EUV resist at Selete** [7140-07]
D. Kawamura, K. Kaneyama, S. Kobayashi, H. Oizumi, T. Itani, Semiconductor Leading Edge Technologies, Inc. (Japan)
- 7140 09 **Methodology of flare modeling and compensation in EUVL** [7140-08]
I. Kim, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); H. Kang, ASML (Korea, Republic of); C. Park, J.-O. Park, J. Lee, J. Park, D. Goo, J. Yeo, S.-W. Choi, W. Han, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)

EMERGENT LITHOGRAPHIC TECHNOLOGY

- 7140 0A **What is the strongest candidate in lithography for 2x nm HP and beyond? (Invited Paper)** [7140-09]
K. Hashimoto, I. Yoneda, T. Koshiba, S. Mikami, T. Ota, M. Ito, T. Nakasugi, T. Higashiki, Toshiba Corp. (Japan)
- 7140 0C **Nano-imprint fabrication and light extraction simulation of photonic crystals on OLED** [7140-11]
J. W.-C. Yu, National Cheng Kung Univ. (Taiwan); Y.-B. Guo, Toppan CFI Co., Ltd. (Taiwan); J.-Y. Chen, Hsing Kuo Univ. of Management (Taiwan); F. C.-N. Hong, National Cheng Kung Univ. (Taiwan)

CD METROLOGY

- 7140 0F **The CD metrology perspectives and future trends (Invited Paper)** [7140-14]
J. Foucher, CEA-LETI (France); E. Pargon, M. Martin, LTM/CNRS (France); V. Farys, STMicroelectronics (France); S. Bécu, CEA-LETI (France); L. Babaud, LTM/CNRS (France) and STMicroelectronics (France)

- 7140 OG **Optimizing integrated optical CD monitoring by floating pre-process variations in a complex multi-layer structure** [7140-15]
M. Strobl, L. Huang, Inotera Memories Inc. (Taiwan); A. Li, Tokyo Electron Taiwan Ltd. (Taiwan); Y. Luo, Y. Wen, Timbre Technology, Inc. (United States)
- 7140 OH **Improving sidewall profile metrology with enhanced 3D-AFM** [7140-16]
T. Bao, L. Mininni, D. Dawson, Veeco Instruments Inc. (United States)
- 7140 OI **Accurate dimensional characterization of periodic structures by spectroscopic Mueller polarimetry** [7140-17]
M. Foldyna, A. De Martino, Lab. de Physique des Interfaces et des Caurel Minces, CNRS, Ecole Polytechnique (France); D. Cattelan, Groupe HORIBA (France); F. Bogeat, C. Licitra, J. Foucher, P. Barritault, J. Hazart, CEA-LETI, MINATEC (France)
- 7140 OJ **Characterization of inhomogeneous samples by spectroscopic Mueller polarimetry** [7140-18]
M. Foldyna, A. De Martino, R. Ossikovski, E. Garcia-Cavrel, CNRS, Lab. de Physique des Interfaces et des Caurel Minces, Ecole Polytechnique (France); D. Cattelan, Groupe HORIBA (France); C. Licitra, CEA LETI MINATEC (France)

PROCESS CONTROL AND METROLOGY

- 7140 OK **An update on the DPL overlay discontinuity (Invited Paper)** [7140-19]
M. Adel, KLA-Tencor Corp., Israel (Israel)
- 7140 OM **Advance overlay correction beyond 32nm DRAM process** [7140-21]
C. T. Hung, C. P. Hsia, T. S. Cheng, C. Y. Huang, W. B. Wu, C. L. Shih, Nanya Technologies Corp. (Taiwan)
- 7140 ON **A comprehensive look at a new metrology technique to support the needs of lithography performance in near future** [7140-22]
J. Hu, C.-M. Ke, W. Wang, J. Huang, H. L. Chung, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan); C. R. Liang, V. Shih, H. H. Liu, H. J. Lee, L. G. Teng, Y. D. Fan, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan); M. van der Schaar, K. Yuan, V. Wang, C. Wang, M. Shahrjerdy, A. Fuchs, K. Bhattacharyya, K. van der Mast, ASML (Netherlands)

LITHOGRAPHY PROCESS CONTROL

- 7140 OQ **Focus and dose control for high volume manufacturing (Invited Paper)** [7140-25]
H. Ina, K. Sentoku, Canon Inc. (Japan)
- 7140 OR **Lithography hotspot discovery at 70nm DRAM 300mm fab: process window qualification using design base binning** [7140-26]
D. Chen, Inotera Memories Inc. (Taiwan); D. Chen, KLA-Tencor Corp. (United States); R. Yen, M. Cheng, A. Lan, Inotera Memories Inc. (Taiwan); R. Ghaskadvi, KLA-Tencor Corp. (United States)

- 7140 OS **Accelerating 32nm BEOL technology development by advanced wafer inspection methodology** [7140-27]
P. R. Jeng, C. L. Lin, S. Jang, M. S. Liang, Taiwan Semiconductor Manufacturing Co., Ltd. (Taiwan); W. Chen, D. Tsui, D. Chen, H. Chen, C. Young, E. Chang, KLA-Tencor Corp. (United States)
- 7140 OU **Reducing capital and labor costs of 193nm lithography monitoring of airborne molecular contamination (AMC) through proactive assessment and implementation of AMC monitoring techniques and strategies** [7140-29]
S. Rowley, Particle Measuring Systems, Inc. (United States); J. Yang, A. Wei, Sunway Scientific Corp. (Taiwan)

DEFECT INSPECTION

- 7140 OW **Advanced inspection methodologies for detection and classification of killer substrate defects** [7140-31]
A. Chen, V. Huang, S. Chen, C. J. Tsai, K. Wu, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan); H. Zhang, KLA-Tencor Corp. (United States); K. Sun, KLA-Tencor Taiwan (Taiwan); J. Saito, KLA-Tencor Corp. (United States); H. Chen, D. Hu, KLA-Tencor Taiwan (Taiwan); M. Li, W. Shen, U. Mahajan, KLA-Tencor Corp. (United States)
- 7140 OX **Electron beam charging of a SiO₂ layer on Si: a comparison between Monte Carlo-simulated and experimental results** [7140-32]
K. Inai, K. Ohya, H. Kuwada, R. Kawasaki, Univ. of Tokushima (Japan); M. Saito, K. Fujihara, T. Hayashi, Tokyo Electron Ltd. (Japan); J. Jau, K. Kanai, Hermes Microvision, Inc. (United States)
- 7140 OY **Advanced technology for after-develop inspection** [7140-33]
Z. Y. Chen, I. C. Chou, J. H. Yang, Taiwan Semiconductor Manufacturing Co., Ltd. (Taiwan); W. Chen, J. Chang, H. Chen, M. Ng, M.-C. Wu, C. Perry-Sullivan, M. Li, KLA-Tencor Corp. (Taiwan)

OPTICAL (IMAGING)

- 7140 10 **An innovative Source-Mask co-Optimization (SMO) method for extending low k₁ imaging** [7140-35]
S. Hsu, L. Chen, Z. Li, S. Park, K. Gronlund, H. Liu, N. Callan, ASML Brion Technologies, Inc. (United States); R. Socha, S. Hansen, ASML TDC (United States)
- 7140 11 **A novel lithography design and verification methodology with patterning failure** [7140-36]
S. Miyoshi, Y. Kobayashi, S. Tanaka, K. Kawano, K. Hashimoto, S. Inoue, Toshiba Corp. (Japan)
- 7140 12 **A new calibration method for latent image fidelity** [7140-37]
E. Barouch, S. L. Knodle, Boston Univ. (United States)
- 7140 13 **An imaging system for extended ArF immersion lithography** [7140-38]
T. Matsuyama, Y. Ohmura, T. Nakashima, Y. Uehara, Nikon Corp. (Japan)

- 7140 14 **Model-based sub-resolution assist features using an inverse lithography method (Best Student Paper Award)** [7140-83]
J.-C. Yu, P. Yu, H.-Y. Chao, National Chiao Tung Univ. (Taiwan)

OPTICAL (IMAGING) II

- 7140 15 **Immersion lithography: its history, current status, and future prospects** [7140-40]
S. Owa, H. Nagasaka, Nikon Corp. (Japan)
- 7140 17 **Patterning performance of hyper NA immersion lithography for 32nm node logic process** [7140-42]
K. Takahata, M. Kajiwar, Y. Kitamura, T. Ojima, M. Satake, H. Fujise, Y. Seino, T. Ema, M. Takakuwa, S. Nakagawa, T. Kono, M. Asano, S. Kyo, A. Nomachi, H. Harakawa, T. Ishida, S. Hasegawa, K. Miyashita, Toshiba Corp. (Japan); T. Murakami, S. Nagahara, K. Takeda, NEC Electronics Corp. (Japan); S. Mimotogi, S. Inoue, Toshiba Corp. (Japan)
- 7140 18 **Orientation Zernike Polynomials: a systematic description of polarized imaging using high NA lithography lenses** [7140-43]
T. Heil, J. Ruoff, J. T. Neumann, M. Totzeck, D. Krähmer, Carl Zeiss SMT AG (Germany); B. Geh, Carl Zeiss SMT AG (Germany) and ASML US, Inc. (United States); P. Gräupner, Carl Zeiss SMT AG (Germany)
- 7140 19 **Resist-based polarization monitoring for 193nm high-numerical aperture lithography** [7140-44]
R. Tu, Benchmark Technologies (United States); G. McIntyre, IBM Advanced Lithography Research (United States)
- 7140 1A **Binary mask optimization for inverse lithography with partially coherent illumination** [7140-87]
X. Ma, G. R. Arce, Univ. of Delaware (United States)
- 7140 1B **Extending KrF lithography beyond 80nm with the TWINSKAN XT:1000H 0.93NA scanner** [7140-46]
W. de Boeij, G. Dicker, M. de Wit, F. Bornebroek, M. Zellenrath, H.-J. Voorma, B. Smeets, R. Toussaint, B. Paarhuis, M. de Jong, ASML Netherlands B.V. (Netherlands); D. Hellweg, K. Kornitzer, Carl Zeiss SMT AG (Germany)

EUV SCANNER AND SOURCES

- 7140 1C **Development of EUV lithography tools at Nikon (Invited Paper)** [7140-47]
K. Murakami, T. Oshino, H. Kondo, H. Chiba, K. Nomura, H. Kawai, Y. Kohama, K. Morita, K. Hada, Y. Ohkubo, T. Miura, Nikon Corp. (Japan)
- 7140 1E **Laser-produced plasma source system development** [7140-49]
D. C. Brandt, I. V. Fomenkov, A. I. Ershov, W. N. Partlo, D. W. Myers, N. R. Böwering, G. O. Vaschenko, O. V. Khodykin, A. N. Bykanov, J. R. Hoffman, C. P. Chrobak, S. N. Srivastava, D. A. Vidusek, S. De Dea, R. R. Hou, Cymer, Inc. (United States)

- 7140 1F **Status of DPP EUV sources development for Beta/HVM** [7140-50]
M. Yoshioka, XTREME technologies GmbH (Germany); P. Zink, Philips Extreme UV GmbH (Germany); G. Schriever, XTREME technologies GmbH (Germany); M. Corthout, Philips Extreme UV GmbH (Germany)

EMERGENT IMAGING TECHNOLOGY

- 7140 1I **A novel curve-fitting procedure for determining proximity effect parameters in electron beam lithography** [7140-53]
C.-H. Liu, H.-T. Ng, P. C. W. Ng, K.-Y. Tsai, National Taiwan Univ. (Taiwan); S.-J. Lin, J.-H. Chen, Taiwan Semiconductor Manufacturing Co., Ltd. (Taiwan)
- 7140 1J **Calculation of three-dimensional profiles of photoresist exposed by localized electric fields of high-transmission metal nano-apertures** [7140-54]
E. Lee, J. W. Hahn, Yonsei Univ. (Korea, Republic of)
- 7140 1K **Study on imaging characterization of ArF high index immersion lithography** [7140-55]
S. Park, J.-T. Park, K. Lee, T.-S. Eom, J.-S. Kim, H.-S. Kim, S.-C. Moon, Hynix Semiconductor Inc. (Korea, Republic of)

EUV INFRASTRUCTURE

- 7140 1N **Influences of various defects on extreme ultraviolet mask** [7140-58]
E.-J. Kim, J.-H. You, Hanyang Univ. (Korea, Republic of); J.-Y. Lee, D.-B. Kim, J.-H. Kim, Dongjin Semichem Co., Ltd. (Korea, Republic of); H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 7140 1Q **Cost of ownership for future lithography technologies** [7140-61]
A. J. Hazelton, Nikon Corp. (Japan); A. Wüest, G. Hughes, L. C. Litt, F. Goodwin, SEMATECH (United States)

LITHO MASK TECHNOLOGY

- 7140 1S **Removal of particles from lithographic masks through plasma-assisted cleaning by metastable atomic neutralization** [7140-63]
W. M. Lytle, D. S. Szybalski, C. E. Das, R. Raju, V. Surla, M. J. Neumann, D. N. Ruzic, Univ. of Illinois at Urbana-Champaign (United States)
- 7140 1T **Application of multi-tone mask technology in photolithographic fabrication of color filter components in LCD** [7140-65]
Y. Takada, M. Fukui, T. Sai, Mitsubishi Chemical Corp. (Japan)
- 7140 1V **Effective solution to reticle haze formation at 193nm lithography** [7140-67]
W.-J. Tseng, S.-H. Chiou, Rexchip Electronics Corp. (Taiwan); M.-C. Chiu, P.-S. Lee, Gudeng Precision Industrial Co., Ltd. (Taiwan)
- 7140 1W **Robust mask design with defocus variation using inverse synthesis (Best Student Paper Award)** [7140-88]
N. Jia, The Univ. of Hong Kong (Hong Kong China); A. K. Wong, Magma Design Automation (United States); E. Y. Lam, The Univ. of Hong Kong (Hong Kong China)

OPTICAL (DPT)

- 7140 1X **A methodology for double patterning compliant split and design (Invited Paper)** [7140-68]
V. Wiaux, S. Verhaegen, IMEC (Belgium); F. Iwamoto, Panasonic (Japan); M. Maenhoudt, IMEC (Belgium); T. Matsuda, Panasonic (Japan); S. Postnikov, Infineon (Germany); G. Vandenberghe, IMEC (Belgium)
- 7140 1Z **Full-chip pitch/pattern splitting for lithography and spacer double patterning technologies** [7140-70]
T.-B. Chiou, ASML Taiwan Ltd. (Taiwan); R. Socha, ASML (United States); H.-Y. Kang, ASML Korea Co., Ltd. (Korea, Republic of); A. C. Chen, ASML Taiwan Ltd. (Taiwan); S. Hsu, H. Chen, L. Chen, ASML Brion (United States)
- 7140 20 **Alternative technology for double patterning process simplification** [7140-71]
H.-Y. Lim, K.-Y. Jang, J.-H. Kim, S.-G. Lee, S. Park, T.-H. Kim, C.-K. Bok, S.-C. Moon, Hynix Semiconductor Inc. (Korea, Republic of)
- 7140 21 **Challenges of 29nm half-pitch NAND Flash STI patterning with 193nm dry lithography and self-aligned double patterning** [7140-72]
M. C. Chiu, B. S.-M. Lin, M. F. Tsai, Y. S. Chang, M. H. Yeh, T. H. Ying, Powerchip Semiconductor Corp. (Taiwan); C. Ngai, J. Jin, S. Yuen, S. Huang, Y. Chen, L. Miao, K. Tai, A. Conley, I. Liu, Applied Materials, Inc. (United States)

OPTICAL (DPT PROCESS)

- 7140 22 **Mask specification guidelines in spacer patterning technology** [7140-73]
K. Hashimoto, H. Mukai, S. Miyoshi, S. Yamaguchi, H. Mashita, Y. Kobayashi, K. Kawano, T. Hirano, Toshiba Corp. (Japan)
- 7140 23 **Cluster optimization to improve CD control as an enabler for double patterning** [7140-74]
L. Tedeschi, C. Rosslee, Sokuda Co., Ltd. (United States); D. Laidler, P. Leray, K. D'havé, IMEC (Belgium)
- 7140 24 **CD uniformity improvement for 3x nm node devices** [7140-75]
C.-M. Park, H.-B. Kim, H.-D. Kim, H.-W. Kim, C.-H. Kim, J.-O. Park, D. Goo, J. Yeo, S.-W. Choi, W.-S. Han, SAMSUNG Electronics Co., Ltd. (Korea, Republic of); M.-S. Choi, S.-W. Hwang, Korea Univ. (Korea, Republic of)
- 7140 25 **Using scatterometry to improve process control during the spacer pitch splitting process** [7140-76]
S. Corboy, C. MacNaughton, T. Gubiotti, M. Wollenweber, KLA-Tencor Corp. (United States)

ADVANCED EXPOSURE TOOL CONTROL

- 7140 27 **Experimental proximity matching of ArF scanners** [7140-78]
J. Bekaert, L. Van Look, P. De Bisschop, J. Van de Kerkhove, G. Vandenberghe, IMEC vzw (Belgium); K. Schreel, J. Menger, G. Schiffelers, E. Knols, H. van der Laan, R. Willekers, ASML (Netherlands)

- 7140 28 **Exposure tool for 32-nm lithography: requirements and development progress** [7140-79]
A. J. Hazelton, J. Ishikawa, N. Magome, Nikon Corp. (Japan)
- 7140 2A **The impact of illuminator signatures on optical proximity effects** [7140-81]
J. K. Tyminski, S. P. Renwick, Nikon Precision Inc. (United States)

OPTICAL (OPC)

- 7140 2B **Model based pattern matching** [7140-82]
L. S. Melvin III, J. Tuttle, M. Boman, Synopsys, Inc. (United States)
- 7140 2D **Optimization of RET flow using test layout** [7140-84]
Y. Zhang, S. Sethi, K. Lucas, Synopsys, Inc. (United States)
- 7140 2E **Image parameter-based scatter bar optimization** [7140-85]
R. Chou, L.-T. Hsiao, H. Y. Liao, J. Lin, R. Shen, J. Schacht, Mentor Graphics Taiwan, Ltd. (Taiwan); D. Chou, S. Jayaram, P. LaCour, Mentor Graphics Corp. (United States)
- 7140 2G **The divergence of image and resist process metrics** [7140-45]
J. J. Biafore, S. Kapasi, S. A. Robertson, M. D. Smith, KLA-Tencor, FINLE (United States)

NOVEL RESIST MATERIAL AND PROCESSING

- 7140 2H **Pattern freezing process free litho-litho-etch double patterning (Invited Paper)** [7140-90]
T. Ando, M. Takeshita, R. Takasu, Y. Yoshii, J. Iwashita, S. Matsumaru, S. Abe, T. Iwai, Tokyo Ohka Kogyo Co., Ltd. (Japan)
- 7140 2I **Novel embedded barrier layer materials for ArF non-topcoat immersion applications** [7140-91]
D. Wang, C. Wu, C. B. Xu, G. Barclay, P. Trefonas, S. Dinglee, Rohm and Haas Electronic Materials (United States)
- 7140 2J **Reactive liquid crystal materials for optically anisotropic patterned retarders** [7140-93]
R. Harding, I. Gardiner, Merck (United Kingdom); H.-J. Yoon, Merck (United Kingdom) and Merck Advanced Technologies (Korea, Republic of); T. Perrett, O. Parri, K. Skjonnemand, Merck (United Kingdom)
- 7140 2K **Development status of High OD photo resist for CF black matrix** [7140-94]
D. Shiota, A. Katano, M. Shida, K. Uchikawa, Tokyo Ohka Kogyo Co., Ltd. (Japan)

NOVEL RESIST MATERIAL AND PROCESSING II

- 7140 2M **Exposure illuminance dependability in the lithography characteristic of color resist for LCD color filter** [7140-96]
M. Yashiro, M. Ohta, Toyo Ink Mfg. Co., Ltd. (Japan)
- 7140 2O **Development of photosensitive silsesquioxane** [7140-98]
Y. Tashiro, T. Sekito, T. Iwata, D. Yokoyama, T. Nonaka, AZ Electronic Materials Japan (Japan)

- 7140 2P **Grazing incidence ion beams for reducing LER** [7140-99]
C. R. M. Struck, M. J. Neumann, R. Raju, Univ. of Illinois at Urbana-Champaign (United States);
R. L. Bristol, Intel Corp. (United States); D. N. Ruzic, Univ. of Illinois at Urbana-Champaign
(United States)
- 7140 2Q **Use of spin-on-hard mask materials for nano scale patterning technology** [7140-109]
W.-H. Wu, E. Y. Chang, National Chiao Tung Univ. (Taiwan); H.-S. Cheon, S. K. Kim, H. M. Cho,
K.-H. Yoon, J. S. Kim, T. Chang, S. Shin, Samsung Cheil Industries, Inc. (Korea, Republic of)

ADVANCED MATERIALS

- 7140 2R **Development of spin-on carbon hardmasks with comparable etch resistance to Amorphous Carbon Layer (ACL)** [7140-100]
H.-S. Cheon, K.-H. Yoon, M.-S. Kim, S. B. Oh, J. Y. Song, N. Tokareva, J. S. Kim, T. Chang,
SAMSUNG Cheil Industries, Inc. (Korea, Republic of)
- 7140 2S **High Si content BARC for applications in dual BARC systems such as tri-layer patterning**
[7140-101]
J. Kennedy, S.-Y. Xie, Z.-Y. Wu, R. Katsanes, K. Flanigan, Honeywell Co., Ltd. (United States);
K. Lee, Honeywell Co., Ltd. (Taiwan); M. Slezak, N. Fender, JSR Micro, Inc. (United States);
J. Takahashi, JSR Inc. (Taiwan)
- 7140 2T **Spin-on trilayer scheme: enabling materials for extension of ArF immersion lithography to 32nm node and beyond** [7140-102]
R. Zhang, A. G. Timko, L. Pylyneva, J. Loch, H. Wu, D. J. Abdallah, R. A. Collett, Y. Wei,
D. Rahman, D. S. McKenzie, P.-H. Lu, M. Neisser, AZ Electronic Materials (United States)
- 7140 2U **BARC technology for 1.35 NA lithography** [7140-103]
M. Reilly, G. G. Zhang, K. Spizuoco, Rohm and Haas Electronic Materials (United States)
- 7140 2V **Optimization of optical properties of silicon-based anti-reflective spin-on hardmask materials** [7140-104]
S. K. Kim, H. M. Cho, C. Woo, S. R. Koh, M. Kim, H. C. Yoon, W. Lee, S.-W. Shin, J. S. Kim,
T. Chang, SAMSUNG Cheil Industries, Inc. (Korea, Republic of)

ADVANCED MATERIALS II

- 7140 2W **Acid-degradable hyperbranched polymer and its application in bottom anti-reflective coatings** [7140-106]
R.-M. L. Mercado, H. Xu, J. A. Lowes, J. D. Meador, D. J. Guerrero, Brewer Science, Inc.
(United States)
- 7140 2X **Bottom anti-reflective coating for hyper NA process: theory, application, and material development** [7140-108]
H. Yao, J. Cho, J. Yin, S. Mullen, G. Lin, M. Neisser, R. Dammel, AZ Electronic Materials US
Corp. (United States)
- 7140 2Y **A technique for rapid elimination of microbubbles for photochemical filter startup** [7140-110]
A. Wu, W. Chow, Entegris, Inc. (United States)

- 7140 22 **The first on-site evaluation of a new filter optimized for TARC and developer** [7140-111]
T. Umeda, Nihon Pall, Ltd. (Japan); T. Ishibashi, Renesas Technology Corp. (Japan);
A. Nakamura, J. Ide, M. Nagano, K. Omura, Renesas Semiconductor Engineering Corp.
(Japan); S. Tsuzuki, T. Numaguchi, Nihon Pall, Ltd. (Japan)

POSTER SESSION

- 7140 30 **Optimization of mask manufacturing rule check constraint for model based assist feature generation** [7140-64]
S. Shim, Y. Kim, Y. Chun, S. Lee, S. Lee, S. Choi, W. Han, S. Chang, S. Yoon, H. Kim, W. Ki,
S. Woo, H. Cho, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 7140 31 **The noble resists composed of cationic and anionic polymerizable PAGs** [7140-92]
J. H. Oh, D. C. Seo, H. S. Joo, S. D. Jung, J. H. Kim, S. J. Lee, R. R. Park, J. Han, J. H. Park, Korea
Kumho Petrochemical Co., Ltd. (Korea, Republic of)
- 7140 32 **Practical requirement for reflectivity control in sub 30nm device using high NA immersion lithography** [7140-105]
Y.-K. Jang, S. Han, H. Kim, J.-Y. Yoon, S. Lee, K. Yoon, S. Oh, S.-W. Choi, W.-S. Han,
SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 7140 33 **Application of exposure simulation system to reduce isolated-dense bias by using annular off-axis illumination** [7140-112]
Y.-N. Shih, Yuan Ze Univ. (Taiwan) and Photronics Semiconductor Mask Corp. (Taiwan);
N.-P. Chen, Yuan Ze Univ. (Taiwan)
- 7140 34 **Resolution enhancement techniques for contact hole printing of sub-50nm memory device** [7140-113]
H. Shin, T. You, M. Yoo, J. Choi, K. Yang, C. Park, D. Yim, Hynix Semiconductor Inc. (Korea,
Republic of)
- 7140 35 **Process capability comparison between LELE DPT and spacer for NAND flash 32nm and below** [7140-114]
S. Tseng, A. C. Chen, ASML (Taiwan)
- 7140 37 **A cost effective spin on sidewall material alternative to the CVD sidewall process** [7140-116]
D. Maruyama, B.-C. Ho, S. Yoon, R. Sakamoto, Y. Sakaida, K. Hashimoto, N. Fujitani,
H. Yaguchi, K. Matsubara, Nissan Chemical Industries, Ltd. (Japan)
- 7140 38 **22nm 1:1 line and space patterning by using double patterning and resist reflow process** [7140-117]
J.-M. Park, J.-H. Yoo, J.-Y. Hong, I. An, H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 7140 39 **193-nm immersion lithography for high volume manufacturing using novel immersion exposure tool and coater/developer system** [7140-118]
S. Wakamizu, H. Kyouda, Tokyo Electron Kyushu Ltd. (Japan); K. Nakano, T. Fujiwara, Nikon
Corp. (Japan)

- 7140 3A **Defect transfer from immersion exposure process to etching process using novel immersion exposure and track system** [7140-119]
O. Miyahara, H. Kosugi, Tokyo Electron Kyushu Ltd. (Japan); S. Dunn, Tokyo Electron Ltd. Technology Ctr., America, LLC (United States); Y. van Dommelen, C. Grouwstra, ASML Netherlands B.V. (Netherlands)
- 7140 3C **The limit to 4X EUVL** [7140-121]
K. Takehisa, Lasertec Corp. (Japan)
- 7140 3D **Correction for surface charge induced beam displacement in large area sub-45 nm patterning with FIB lithography** [7140-122]
M. Chung, Southern Taiwan Univ. (Taiwan) and National Cheng Kung Univ. (Taiwan); H.-Y. Lin, J.-H. Tsai, Industrial Technology Research Institute (Taiwan)
- 7140 3E **CD uniformity improvement of sub 60nm contact hole using model based OPC** [7140-123]
H.-S. Yune, Y.-B. Ahn, J.-C. Kim, H.-J. Shin, G. Yoo, J. Moon, B.-S. Nam, D. Yim, Hynix Semiconductor Inc. (Korea, Republic of)
- 7140 3F **Analysis of adsorption effect of absorbent and threshold limit value (TLV) of Q-time for 193nm ArF reticle haze resistance** [7140-124]
F.-S. Chu, S.-H. Chiou, Rexchip Electronics Corp. (Taiwan)
- 7140 3G **The APC (Advanced Process Control) procedure for process window and CDU improvement using DBMs** [7140-125]
J. Kim, T. Lee, A. Jung, G. Yoo, H. Yang, D. Yim, S. Park, Hynix Semiconductor Inc. (Korea, Republic of); J. Seo, B. Park, T. Hasebe, M. Yamamoto, NanoGeometry Research Inc. (Japan)
- 7140 3H **Application automatic focusing with DVD pickup head in FPD substrate inspection** [7140-126]
C. M. Tseng, National Sun Yat-Sen Univ. (Taiwan) and Metal Industries Research and Development Ctr. (Taiwan); C. Y. Chung, Metal Industries Research and Development Ctr. (Taiwan); S. C. Chiu, C. W. Yen, National Sun Yat-Sen Univ. (Taiwan)
- 7140 3J **Developing loading effect on lithography I-line process** [7140-128]
T. Huang, W. Wang, C.-Y. Huang, N. Tseng, T.-J. Guo, C.-L. Shih, W.-B. Wu, Nanya Technologies Corp. (Taiwan)
- 7140 3K **Novel process proximity correction by the pattern-to-pattern matching method with DBM** [7140-129]
D. Park, J. Choi, H. Yune, J. Choi, C. Kim, Hynix Semiconductor Inc. (Korea, Republic of); B.-R. Choi, ASML Korea Co., Ltd (Korea, Republic of); D. Yim, Hynix Semiconductor Inc. (Korea, Republic of)
- 7140 3N **Lithography performance and simulation accuracy at different polarization states for sub 40nm node** [7140-132]
K.-Y. Park, ASML Korea Co., Ltd. (Korea, Republic of); H.-Y. Kang, ASML (United States); G. Isai, K. Elbattay, P. van Oorschot, S. Young, ASML Netherlands B.V. (Netherlands); S.-C. Oh, Y.-H. Min, S.-G. Hong, Y.-T. Park, ASML Korea Co., Ltd. (Korea, Republic of)

- 7140 3R **Considering mask pellicle effect for more accurate OPC model at 45nm technology node** [7140-136]
C.-H. Wang, Q. Liu, Semiconductor Manufacturing International Corp. (China); L. Zhang, Mentor Graphics Corp. (China)
- 7140 3U **Acid diffusion length dependency for 32-nm node attenuated and chromeless phase shift mask** [7140-139]
J.-H. You, Y.-M. Kang, M. Jung, H.-K. Oh, Hanyang Univ. (Korea, Republic of)
- 7140 3X **Cycloolefin effect in cycloolefin-(meth)acryl copolymer** [7140-142]
H. S. Lim, D. C. Seo, C. S. Lee, S. W. Park, S. J. Kim, D. H. Shin, J. B. Shin, J. H. Park, Korea Kumho Petrochemical Co., Ltd. (Korea, Republic of)
- 7140 3Y **Spacer double patterning technique for sub-40nm DRAM manufacturing process development** [7140-143]
W. Shiu, W. Ma, H. W. Lee, J. S. Wu, Y. M. Tseng, K. Tsai, C. T. Liao, A. Wang, A. Yau, Y. R. Lin, Y. L. Chen, T. Wang, W. B. Wu, C. L. Shih, Nanya Technology Corp. (Taiwan)
- 7140 3Z **Development of multi-layer process materials for hyper-NA lithography process** [7140-144]
Y. Sakaida, M. Nakajima, T. Shinjo, K. Hashimoto, Nissan Chemical Industries, Ltd. (Japan)
- 7140 41 **CD control enhancement by laser bandwidth stabilization for advanced lithography application** [7140-146]
R. C. Peng, T. Wu, K. W. Chang, C. P. Yeh, H. H. Liu, H. J. Lee, J. Lin, Taiwan Semiconductor Manufacturing Corp. (Taiwan); A. Chang, B. S.-M. Lin, Cymer Inc. (Taiwan)
- 7140 42 **Analysis of the effect of laser bandwidth on imaging of memory patterns** [7140-147]
N. Seong, Cymer, Inc. (United States); I. Kim, D. Kang, S.-H. Lee, J. Choi, SAMSUNG Electronics Co., Ltd. (Korea, Republic of)
- 7140 43 **Throughput improvement from routing reduction by using CPE (correction per exposure)** [7140-148]
R. C. Chang, J.-C. Yang, C.-H. Chen, C.-C. Lin, Inotera Memories Inc. (Taiwan); C. Wang, W. Lin, C.-C. Chen, ASML Taiwan Ltd. (Taiwan)

Author Index

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Gary Zhang, Rohm and Haas Electronic Materials (United States)

Session Chairs

1 Plenary Session

Alek C. Chen, ASML Taiwan Ltd. (Taiwan)

- 2 EUVL Technology
Kuen-Yu Tsai, National Taiwan University (Taiwan)
Kohji Hashimoto, Toshiba Corp. (Japan)
- 3 Emergent Lithographic Technology
Masaomi Kameyama, Nikon Corp. (Japan)
Hye-Keun Oh, Hanyang University (Korea, Republic of)
- 4 CD Metrology
Hideki Ina, Canon Inc. (Japan)
Vincent Wiaux, IMEC (Belgium)
- 5 Process Control and Metrology
Kafai Lai, IBM Microelectronics Div. (United States)
Tsann-Bim Chiou, ASML Taiwan Ltd. (Taiwan)
- 6 Lithography Process Control
Michael E. Adel, KLA-Tencor Israel (Israel)
Masaomi Kameyama, Nikon Corp. (Japan)
- 7 Defect Inspection
Edmund Y. Lam, The University of Hong Kong (Hong Kong, China)
Jan C. H. Mulken, ASML Netherlands B.V. (Netherlands)
- 8 Optical (Imaging)
Hideki Ina, Canon Inc. (Japan)
Vincent Wiaux, IMEC (Belgium)
- 9 Optical (Imaging) II
Kohji Hashimoto, Toshiba Corp. (Japan)
Tsann-Bim Chiou, ASML Taiwan Ltd. (Taiwan)
- 10 EUV Scanner and Sources
Jack J. H. Chen, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
Kuen-Yu Tsai, National Taiwan University (Taiwan)
- 11 Emergent Imaging Technology
Nigel R. Farrar, Cymer, Inc. (United States)
Hye-Keun Oh, Hanyang University (Korea, Republic of)
- 12 EUV Infrastructure
Eric Hendrickx, IMEC (Belgium)
Jack J. H. Chen, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)

- 13 Litho Mask Technology
Naoya Hayashi, Dai Nippon Printing Co., Ltd. (Japan)
Hoyoung Kang, ASML Korea Co., Ltd. (Korea, Republic of)
- 14 Optical (DPT)
Joost P. M. Bekaert, IMEC (Belgium)
Kuen-Yu Tsai, National Taiwan University (Taiwan)
- 15 Optical (DPT Process)
Hideki Ina, Canon Inc. (Japan)
Ho-Young Kang, ASML Korea Co., Ltd. (Korea, Republic of)
- 16 Advanced Exposure Tool Control
Jan C. H. Mulken, ASML Netherlands B.V. (Netherlands)
Nigel R. Farrar, Cymer, Inc. (United States)
- 17 Optical (OPC)
Tsann-Bim Chiou, ASML Taiwan Ltd. (Taiwan)
Eric Hendrickx, IMEC (Belgium)
- 18 Novel Resist Material and Processing
Junichi Onodera, Tokyo Ohka Kogyo Co., Ltd. (Japan)
Wen-Yi Lin, AU Optronics Corp. (Taiwan)
- 19 Novel Resist Material and Processing II
Charles Chang, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
Shuji S. Dinglee, Rohm and Haas Electronic (Taiwan)
- 20 Advanced Materials
Charles Chang, Taiwan Semiconductor Manufacturing Co. Ltd. (Taiwan)
Wen-Yi Lin, AU Optronics Corp. (Taiwan)
- 21 Advanced Materials II
Junichi Onodera, Tokyo Ohka Kogyo Co., Ltd. (Japan)
Shuji S. Dinglee, Rohm and Haas Electronic (Taiwan)